

**GROWTH AND CHARACTERIZATION OF GaN
NANOSTRUCTURES AND AlGaN/GaN
HETEROSTRUCTURES FOR DEVICE APPLICATIONS**

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INDIAN INSTITUTE OF TECHNOLOGY DELHI

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NANOSTRUCTURES AND AlGaN/GaN
HETEROSTRUCTURES FOR DEVICE APPLICATIONS**

by

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Submitted

in fulfilment of the requirements of the degree of Doctor of Philosophy

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CERTIFICATE

This is to certify that the thesis entitled “**Growth and Characterization of GaN nanostructures and AlGaIn/GaN Heterostructures for Device Applications**” being submitted by **Ms. Mansi Agrawal** to Indian Institute of Technology Delhi, New Delhi, for the award of the degree of **Doctor of Philosophy** is a record of bonafide research work carried out by her. She has worked under our supervision and guidance and has fulfilled the requirements for the submission of this thesis, which in our opinion has reached the requisite standard. The results contained in this thesis have not been submitted, in part or full, to any other University or Institute for the award of any degree/diploma.



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ABSTRACT

The technological advancement and new device concepts in using semiconducting materials such as III-nitrides with exceptional electronic and optical properties have attracted substantial interest worldwide. One of the semiconducting materials is gallium nitride, belonging to the family of III-nitrides and a wide bandgap (3.42eV) semiconductor. It has a diverse range of applications, including military, high power, automobile and optoelectronic applications. The possibility to grow heterostructures (AlGa_N/Ga_N) is another advantage of Ga_N. A 2DEG is formed in AlGa_N/Ga_N heterostructures resulting from strong spontaneous and piezoelectric polarisation, make them suitable for the next generation high electron mobility transistors. Their efficient device performance is significantly influenced by the surface of these heterostructures. Another significant problem with Ga_N is the absence of a native substrate, which leads to threading dislocations (10^8 cm^{-2} - 10^{10} cm^{-2}) with high density. However, Ga_N nanowires are one of the most probable solutions to the lattice mismatch problem. The present thesis is focussed on the growth and characterisation of gallium nitride nanowires on high index silicon substrates, to investigate how surface treatments affect Ga_N epitaxial films and AlGa_N/Ga_N heterostructures in order to solve device-related issues caused by surface-related problems, and fabricate AlGa_N/Ga_N circular HEMTs on 200 mm silicon and 3" sapphire wafers for sensing applications as the circular geometry provides a large sensing area.

In the present work, firstly MBE technique was used for the growth of gallium nitride nanowires on high index Si (211) substrates without using any catalyst. The synthesis process started with the nitridation of the Si (211) substrates which was carried out at 1170°C. The nitridation time of the Si (211) substrates was then optimised for the growth of the nanowires. The stepped nature of Si (211) substrates resulted in preferential orientation of the nanowires. The nanowires were characterised using various structural, morphological and optical techniques. The length of the nanowires is approximately 450 nm. The diameter of gallium nitride nanowires had a range from 20 nm to 80 nm. FESEM results confirmed that GaN nanowires are highly dense and oriented at 70° with respect to Si (211) substrate. The UV and NO_x gas sensing application of the nanowires were also investigated. The nanowires showed a response of 2.2 % to UV and 24% to NO_x gas with a fast recovery and excellent reproducibility.

Further growth and characterisation of heterostructures based upon MoS₂-GaN nanowires on Si (111) substrates were carried out. Their structural and vibrational properties were studied. PAMBE technique was used to grow GaN nanowires on Si (111) substrates followed by the deposition of 2D MoS₂ layers on the nanowires by CVD technique. SEM results confirmed that GaN nanowires are decorated by triangular shaped MoS₂ domains. The numbers of MoS₂ layers were investigated using Raman spectroscopy. The difference between A_{1g} and E_{2g} Raman peaks is 24.8 cm⁻¹ which indicates the presence of few monolayers of MoS₂ on GaN nanowires.

Thus, the results obtained indicate that GaN nanowires can be integrated with two dimensional MoS₂ layers.

The effect of chemical surface treatments in GaN epitaxial films and AlGa_N/GaN heterostructures is investigated. Hot phosphoric acid treatment was used for polarity determination in gallium nitride films which leads to the formation of hexagonal pits in Ga-polar films and dodecagonal pyramids in N-polar films as studied using FESEM. In addition, it was observed that the hydrogen peroxide treatment in AlGa_N/GaN heterostructures results in passivation of AlGa_N surface and hence can result in improving the device performance. Hydrogen peroxide treatment leads to the increase in PL intensity and decrease in surface barrier height by 0.19 eV as assessed by XPS. Surface photovoltage spectroscopy, which uses surface photovoltage as a parameter, was also used to investigate the impact of hydrogen peroxide on the AlGa_N surface.

Gateless circular HEMTs on 200 mm silicon substrates and circular HEMTs on 3" sapphire substrates were fabricated respectively for sensing applications. The saturated drain current (I_{Dsat}) of gateless HEMTs was found to be around 383 mA with a knee voltage at around 6.2 V. The gateless circular HEMTs showed a response ($\delta I_{DS}/I_{DS}$) of about 0.694% at source drain voltage of 100 mV along with a slow recovery time of 2394s due to persistent photoconductivity effect to ultraviolet light at room temperature with excellent repeatability. In addition for the AlGa_N/GaN circular HEMTs on sapphire wafers with Pd as a gate metal I_{DSS} was found to be 0.95 A/mm with a knee voltage of 5.6 V. The hydrogen and UV sensing applications of

circular HEMTs were then studied. The HEMTs exhibited a sensitivity of 12.67 % to hydrogen gas and 4.58% to ultraviolet light at room temperature respectively.

The results of the present thesis show that GaN nanowires on high index silicon substrates have immense potential for sensing applications and circular HEMTs are desirable candidates for sensing applications as they provide a large surface area in comparison to conventional HEMTs.

सार

वैश्विक तकनीकी प्रगति ने दुनिया भर में असाधारण इलेक्ट्रॉनिक और ऑप्टिकल गुणों के साथ III-नाइट्राइड जैसे सेमीकंडक्टिंग सामग्रियों पर आधारित उपकरणों की महत्वपूर्ण रुचि को आकर्षित किया है। सेमीकंडक्टिंग सामग्रियों में से एक गैलियम नाइट्राइड है, जो III-नाइट्राइड्स के परिवार से संबंधित है और एक विस्तृत बैंडगैप (3.42eV) सेमीकंडक्टर है। इसमें सैन्य, उच्च शक्ति, ऑटोमोबाइल और ऑप्टोइलेक्ट्रॉनिक अनुप्रयोगों सहित विविध प्रकार के अनुप्रयोगों की विस्तृत श्रृंखला है। हेटरोस्ट्रक्चर (AlGaIn/GaN) के बनाने की संभावना GaN का एक और फायदा है। AlGaIn/GaN हेटरोस्ट्रक्चर में 2DEG बनता है, जो मजबूत सहज और पीजोइलेक्ट्रिक ध्रुवीकरण से उत्पन्न होता है, जो उन्हें अगली पीढ़ी के उच्च इलेक्ट्रॉन गतिशीलता ट्रांजिस्टर के लिए उपयुक्त बनाता है। उनका कुशल उपकरण प्रदर्शन इन हेटरोस्ट्रक्चर की सतह से काफी प्रभावित होता है। GaN के साथ एक अन्य महत्वपूर्ण समस्या एक देशी सबस्ट्रेट की अनुपस्थिति है, जो उच्च घनत्व के साथ अव्यवस्थाओं (10^8 cm^{-2} - 10^{10} cm^{-2}) को फैलाने की ओर ले जाती है। हालांकि, GaN नैनोवायर इस समस्या के सबसे संभावित समाधानों में से एक हैं। प्रस्तुत शोध कार्य उच्च सूचकांक सिलिकॉन सबस्ट्रेट्स पर गैलियम नाइट्राइड नैनोवायरों के विकास और लक्षण वर्णन पर केंद्रित है, यह जांच करने के लिए कि सतह से संबंधित समस्याओं के कारण डिवाइस से संबंधित मुद्दों को हल करने के लिए सतह के उपचार GaN एपिटैक्सियल फिल्मों और AlGaIn/GaN हेटरोस्ट्रक्चर को कैसे प्रभावित करते हैं, और गढ़ते हैं। और संवेदन अनुप्रयोगों के लिए 200 मिमी सिलिकॉन और 3 "नीलम वेफर्स पर AlGaIn / GAN परिपत्र HEMT का निर्माण किया गया क्योंकि परिपत्र ज्यामिति एक बड़ा संवेदन क्षेत्र प्रदान करती है।

वर्तमान कार्य में, किसी उत्प्रेरक का उपयोग किए बिना उच्च सूचकांक Si (211) सबस्ट्रेट्स पर गैलियम नाइट्राइड नैनोवायर्स के विकास के लिए सबसे पहले एमबीई तकनीक का उपयोग किया गया था। संश्लेषण प्रक्रिया Si (211) सबस्ट्रेट्स के नाइट्रिडेशन के साथ शुरू हुई जो 1170° C पर किया गया था। Si (211) सबस्ट्रेट्स का नाइट्रिडेशन समय नैनोवायरों के विकास के लिए अनुकूलित किया गया था। Si (211) सबस्ट्रेट्स की चरणबद्ध प्रकृति के परिणामस्वरूप नैनोवायरों का अधिमान्य अभिविन्यास हुआ। नैनोवायरों को विभिन्न

संरचनात्मक, रूपात्मक और ऑप्टिकल तकनीकों का उपयोग करके चित्रित किया गया था। नैनोवायरों की लंबाई लगभग 450 nm है। गैलियम नाइट्राइड नैनोवायरों के व्यास की सीमा 20 nm से 80 nm तक थी। FESEM के परिणामों ने पुष्टि की कि GaN नैनोवायर अत्यधिक सघन हैं और Si (211) सबस्ट्रेट के संबंध में 70° पर उन्मुख हैं। नैनोवायरों के यूवी और एनओएक्स गैस सेंसिंग एप्लिकेशन की भी जांच की गई। नैनोवायरस ने यूवी के लिए 2.2% और एनओएक्स गैस के लिए 24% की तेजी से रिकवरी और उत्कृष्ट प्रजनन क्षमता के साथ प्रतिक्रिया दी।

Si (111) सबस्ट्रेट्स पर MoS₂-GaN नैनोवायरस पर आधारित हेटरोस्ट्रक्चर का आगे विकसित और निरूपित किया गया और उनके संरचनात्मक और कंपन गुणों का अध्ययन किया गया। PAMBE तकनीक का उपयोग Si (111) सबस्ट्रेट्स पर GaN नैनोवायरों को विकसित करने के लिए किया गया था, जिसके बाद CVD तकनीक द्वारा नैनोवायरस पर 2D MoS₂ परतों का निक्षेपण किया गया। SEM परिणामों ने पुष्टि की कि GaN नैनोवायरों को त्रिकोणीय आकार के MoS₂ डोमेन से सजाया गया है। रमन स्पेक्ट्रोस्कोपी का उपयोग करके MoS₂ परतों की संख्या की जांच की गई। A_{1g} और E_{2g} रमन चोटियों के बीच का अंतर 24.8 cm⁻¹ है जो GaN नैनोवायरों पर MoS₂ के कुछ मोनोलेयर्स की उपस्थिति को इंगित करता है। इस प्रकार, प्राप्त परिणाम बताते हैं कि GaN नैनोवायरों को दो आयामी MoS₂ परतों के साथ एकीकृत किया जा सकता है।

अध्ययन के अगले चरण में GaN एपीटैक्सियल फिल्मों और AlGa_{0.3}N/GaN हेटरोस्ट्रक्चर में रासायनिक सतह के उपचार के प्रभाव का अन्वेषण किया गया है। गर्म फॉस्फोरिक एसिड उपचार का उपयोग ध्रुवता निर्धारण के लिए किया गया था, जो गैलियम नाइट्राइड फिल्मों का निर्धारण करता था, जो Ga-ध्रुवीय फिल्मों में हेक्सागोनल गड्ढों के निर्माण की ओर जाता है और N-ध्रुवीय फिल्मों में डोडेकागोनल पिरामिड के रूप में FESEM का उपयोग करके अध्ययन किया जाता है। इसके अलावा, यह देखा गया कि AlGa_{0.3}N/GaN हेटरोस्ट्रक्चर में हाइड्रोजन पेरोक्साइड उपचार के परिणामस्वरूप AlGa_{0.3}N सतह निष्क्रिय हो जाती है और इसलिए डिवाइस के प्रदर्शन में सुधार हो सकता है। हाइड्रोजन पेरोक्साइड उपचार से पीएल तीव्रता में वृद्धि होती है और एक्सपीएस द्वारा मूल्यांकन के अनुसार सतह बाधा ऊंचाई में 0.19 eV की कमी होती है। भूतल

फोटोवोल्टेज स्पेक्ट्रोस्कोपी, जो एक पैरामीटर के रूप में सतह फोटोवोल्टेज का उपयोग करता है, का उपयोग AlGa_N सतह पर हाइड्रोजन पेरोक्साइड के प्रभाव की जांच के लिए भी किया गया था।

इसके अलावा, 200 मिमी सिलिकॉन सबस्ट्रेट्स पर गेटलेस सर्कुलर एचईएमटी और 3" नीलम सबस्ट्रेट्स पर सर्कुलर एचईएमटी क्रमशः सेंसिंग अनुप्रयोगों के लिए तैयार किए गए थे। गेटलेस एचईएमटी का संतृप्त ड्रेन करंट (आईडीसैट) लगभग 6.2 V पर नी वोल्टेज के साथ लगभग 383 mA पाया गया था। गेटलेस सर्कुलर एचईएमटी ने उत्कृष्ट पुनरावृत्ति के साथ कमरे के तापमान पर पराबैंगनी प्रकाश के लिए लगातार फोटोकंडक्टिविटी प्रभाव के कारण 2394s के धीमे रिकवरी समय के साथ 100 mV के स्रोत ड्रेन वोल्टेज पर लगभग 0.694% की प्रतिक्रिया ($\delta IDS/IDS$) दिखाई। इस के अलावा गेट मेटल के रूप में पीडी के साथ नीलम वेफर्स पर AlGa_N/Ga_N सर्कुलर एचईएमटी में 5.6 V के नी वोल्टेज के साथ आईडीएसएस 0.95 A/mm पाया गया। इसके बाद सर्कुलर एचईएमटी के हाइड्रोजन और यूवी सेंसिंग अनुप्रयोगों का अध्ययन किया गया। एचईएमटी ने क्रमशः कमरे के तापमान पर हाइड्रोजन गैस के लिए 12.67% और पराबैंगनी प्रकाश के लिए 4.58% की संवेदनशीलता प्रदर्शित की।

इस प्रकार, शोध अध्ययन के परिणाम बताते हैं कि उच्च सूचकांक सिलिकॉन सबस्ट्रेट्स पर विकसित किये गए Ga_N नैनोवायरों में संवेदन अनुप्रयोगों के लिए अपार संभावनाएं हैं और संवेदन अनुप्रयोगों के लिए सर्कुलर एचईएमटी में पारंपरिक एचईएमटी की तुलना में बड़े सतह क्षेत्र के कारण सेंसिंग एप्लिकेशन के लिए संभावनाएं हैं।

Table of Contents

Certificate	i
Acknowledgements	iii
Abstract	vii
Abstract (Hindi)	xi
Table of Contents	xv
List of Figures	xxi
List of Tables	xxv
List of Symbols and Abbreviations	xxvii

Chapter 1 Introduction

1.1	GaN and its properties an overview	2
1.2	Substrates for GaN.....	3
1.3	GaN nanostructures	6
1.4	Advantages of PAMBE technique for the growth of GaN nanostructures.....	9
1.5	MoS ₂ -GaN heterostructures	12
1.6	AlGa _N /Ga _N high electron mobility transistors (HEMTs).....	15
1.7	AlGa _N /Ga _N HEMTs based sensors	19
1.8	Objectives of the thesis work	21
1.9	Thesis organisation	22
1.10	References.....	25

Chapter 2 Experimental Techniques

2.1	Synthesis Techniques	35
2.1.1	Molecular Beam Epitaxy(MBE)	35
2.1.2	Chemical Vapor Deposition(CVD)	39
2.2	Device Fabrication techniques	41
2.2.1	Photolithography.....	41
2.2.2	Electron Beam Evaporation	42
2.3	Material Characterisation Techniques.....	44
2.3.1	Field Emission Scanning Electron Microscopy (FESEM)	44
2.3.2	High Resolution Transmission Electron Microscopy (HRTEM)	46
2.3.3	Raman Spectroscopy.....	47
2.3.4	Photoluminescence Spectroscopy (PL)	50
2.3.5	Surface Photovoltage Spectroscopy (SPS)	51
2.3.6	X-ray photoelectron Spectroscopy (XPS)	53
2.3.7	Reflection high energy electron diffraction (RHEED)....	55
2.3.8	High resolution X-ray diffraction (HRXRD)	58
2.3.9	Hall Measurements	61
2.4	Device Characterisation Techniques	62
2.4.1	I-V Measurements.....	62
2.4.2	C-V Measurements	63
2.4.3	Sensing Measurements	64
2.5	References	65

Chapter 3 GaN nanowires on Si (211) substrates by Plasma Assisted

Molecular Beam Epitaxy technique for sensing applications

3.1	Introduction	68
3.2	Effect of nitridation time on morphological evolution on Si (211) substrates	71
3.2.1	Experimental Details.....	71
3.2.2	FESEM results of Si (211) substrates after nitridation..	72
3.3	Growth methodology of GaN nanowires on Si (211) wafers	72
3.4	Results for GaN nanowires on Si (211) substrates	76
3.4.1	FESEM Results.....	76
3.4.2	XPS Results	78
3.4.3	HRXRD Results.....	78
3.4.4	Photoluminescence Spectroscopy (PL) Results.....	79
3.4.5	TEM Results	80
3.5	Sensing Applications of GaN nanowires	84
3.5.1	Ultraviolet (UV) Sensing	84
3.5.2	Nitrogen oxide (NO _x) gas sensing	85
3.6	Conclusions	88
3.7	References	89

Chapter 4 Structural and vibrational properties of MoS₂/GaN

nanowires heterostructures on Si (111) substrates

4.1	Introduction	94
4.2	Experimental Section	97
4.3	Results for structural properties of GaN nanowires	100

4.3.1	SEM results	100
4.3.2	X-ray pole figure results	101
4.4	Results for Structural and vibrational properties of MoS ₂ /GaN nanowires.....	102
4.4.1	SEM results	102
4.4.2	HRXRD results	103
4.4.3	Raman spectroscopy results	104
4.5	Conclusions	107
4.6	References	108

Chapter 5 Effect of surface treatments on GaN thin films and AlGa_N/GaN heterostructures

5.1	Introduction	114
5.2	Experimental Details	116
5.3	Results and discussions for the effect of surface treatment to determine the polarity in GaN thin films and AlGa _N /GaN heterostructures.....	119
5.3.1	Effect of phosphoric acid treatment in GaN thin films.....	119
5.3.2	Effect of phosphoric acid treatment and molten potassium hydroxide treatment in GaN/AlGa _N /GaN heterostructures	122
5.4	Results and discussions on the effect of hydrogen peroxide treatment on the structural and optical properties in AlGa _N /GaN heterostructures	126

5.4.1	XPS results	127
5.4.2	Photoluminescence spectroscopy (PL) results	130
5.4.3	Surface photovoltage spectroscopy (SPS) results	132
5.5	Conclusions	135
5.6	References	136

Chapter 6 Fabrication of AlGa_N/Ga_N circular HEMTs for sensing applications

6.1	Introduction	142
6.2	Experimental Details	144
6.2.1	AlGa _N /Ga _N gateless circular HEMT on 200 mm silicon substrates	144
6.2.2	AlGa _N /Ga _N circular HEMT on 3" sapphire substrates.	147
6.3	Results and Discussions of Al _{0.27} Ga _{0.73} N/Ga _N gateless circular HEMTs on 200 mm Si (111) substrates	148
6.3.1	DC characterisation	149
6.3.2	Temperature dependent I-V measurements	151
6.3.3	UV Sensing Applications of gateless circular HEMTs ...	152
6.4	Results and Discussion of AlGa _N /Ga _N circular HEMTs on 3" sapphire substrates.....	156
6.4.1	Hall measurements of AlGa _N /Ga _N epilayers	157
6.4.2	Characterisation of fabricated circular HEMTs	158
6.4.2.1	DC Characterisation	158
6.4.2.2	C-V characterisation.....	163
6.4.3	Sensing applications of circular HEMTs	166

6.4.3.1	Hydrogen sensing.....	166
6.4.3.2	UV sensing	168
6.5	Conclusions	171
6.6	References	172

Chapter 7 Summary, Conclusions and Future Scope

7.1	Summary and Conclusions.....	177
7.2	Future Scope.....	182
List of Publications.....		184
Bio-data.....		188

List of Figures

Figure 1.1	Applications of (a) GaN, (b) 2D-Metal Dichalcogenides, and (c) GaN-MoS ₂ heterostructures	14
Figure 1.2	(a) AlGa _N /Ga _N HEMT epistack, (b) Spontaneous polarisation in Ga _N and AlGa _N before heterostructures formation, (c) Spontaneous and piezoelectric polarisation in AlGa _N /G ₃₆₁ a _N heterostructures, (d) Formation of 2DEG in AlGa _N /Ga _N HEMT, (e) Energy Band diagram of AlGa _N /Ga _N heterostructures.....	17
Figure 1.3	Schematic of AlGa _N /Ga _N HEMT structure with source, gate and drain terminals.....	19
Figure 2.1	Photograph of MBE system at SSPL, Delhi used for the present study	36
Figure 2.2	Schematic of molecular beam epitaxy experimental setup.....	38
Figure 2.3	Schematic of chemical vapor deposition experimental setup	40
Figure 2.4	(a) Photograph of FESEM at SSPL Delhi, and (b) Schematic representation of FESEM measurement setup.....	45
Figure 2.5	Schematic showing elastic (Rayleigh) and inelastic (Stokes and Anti-Stokes) scattering processes in Raman spectroscopy.....	49
Figure 2.6	Photograph of Raman spectrometer at SSPL Delhi used for the present study.....	50
Figure 2.7	Schematic diagram of surface photovoltage spectroscopy measurement setup.....	53
Figure 2.8	Schematic diagram of X-ray photoelectron spectroscopy measurement setup.....	54
Figure 2.9	Photograph of X-ray photoelectron spectroscopy system at SSPL Delhi used for the present study.....	55
Figure 2.10	Schematic diagram of RHEED measurement setup.....	57
Figure 2.11	Schematic of high resolution X-ray diffraction measurement setup.....	59
Figure 2.12	Photograph of high resolution X-ray diffraction system at SSPL Delhi used for the present study.....	61
Figure 3.1	Schematic of terraces and ledges on Si (211).....	70
Figure 3.2	SEM images of Si (211) surface after nitridation at 1170°C for (a) 1 minute, (b) 3 minutes and (c) 15 minutes respectively.....	72
Figure 3.3	RHEED Results: (a) 7 x reconstruction of the clean Si (211) surface, (b) after 15 min nitridation on Si (211) substrate and (c) growth of Ga _N nanowires.....	74
Figure 3.4	Schematic illustration of growth of Ga _N nanowires on Si (211) substrate.....	75
Figure 3.5	Schematic of UV sensing experimental setup.....	76

Figure 3.6	(a) Cross-sectional view and (b), (c), (d) plane view FESEM images of GaN nanowires on Si (211) substrates	77
Figure 3.7	(a) XPS results of Si (211) surface after nitridation at 1170°C for 15 minutes for (a) deconvoluted Si (2p) and (b) deconvoluted N (1s) core level spectra of Si (211) substrate after nitridation for 15 minutes.....	78
Figure 3.8	(a) X-ray pole figure of (0002) reflection GaN nanowires and (b) X-ray rocking curve of (0002) reflection at 18° tilt angle.....	79
Figure 3.9	Photoluminescence spectra of GaN nanowires on Si (211) substrates.....	80
Figure 3.10	(a) SAD pattern showing the epitaxial relationship between Si and GaN, (b) HRTEM image of silicon nitride interlayer, (c) bright field TEM image showing the GaN nanowire and the inset is the micro diffraction pattern along [2-1-10] zone axis, (d) and (e) g-3g weak-beam dark field TEM micrographs with g(0002) and g(01-10) imaging conditions; and (f) GaN nanowire containing multiple basal stacking faults.....	82
Figure 3.11	GaN nanowires exhibiting mosaicity. (a) Bright field TEM image showing the cross-sectional view of the two nanowires near [2-1-10] zone-axis and (b) Micro diffraction pattern showing two overlapped GaN crystals.....	83
Figure 3.12	GaN nanowires on Si (211) substrates upon exposure to UV light.....	85
Figure 3.13	GaN nanowires on Si (211) substrates upon exposure to NO _x gas.....	86
Figure 3.14	Schematic diagram of GaN nanowires NO _x gas sensor...	87
Figure 4.1	(a) 7x7 reconstruction after thermal degassing, (b) after nitridation of Si (111) substrates, and (c) during the growth of GaN nanowires on Si (111) substrates.....	98
Figure 4.2	Schematic illustration of growth process of GaN nanowires on Si (111) substrates.....	99
Figure 4.3	Schematic illustration of growth process of MoS ₂ on GaN nanowires on Si (111) substrates.....	99
Figure 4.4	FESEM images of GaN nanowires on Si (111) substrates (a) Plane view, (b) Cross-sectional view.....	101
Figure 4.5	X-ray pole figure results of GaN nanowires on Si (111) substrates (a) along GaN (002) reflection, (b) along (101) reflection.....	102
Figure 4.6	SEM results of few layers of MoS ₂ /GaN nanowires on Si (111) substrates.....	103
Figure 4.7	HRXRD results of few layers of MoS ₂ /GaN nanowires on Si (111) substrates.....	104
Figure 4.8	Raman spectra of MoS ₂ /GaN nanowires on Si (111) substrates.....	107
Figure 5.1	Schematic of the AlGaN/AlN/GaN HEMT sample 'C'.....	117

Figure 5.2	FESEM images: (a) bare GaN thin film, (b) plane view, (c) tilted view and; (d) magnified image of the phosphoric acid treated sample at 80°C for 10 minutes.....	120
Figure 5.3	HRXRD Rocking curves of phosphoric acid treated GaN thin film: (a) along (002) reflection and (b) along (102) reflection.....	122
Figure 5.4	FESEM images of GaN/AlGa _{0.73} N/GaN heterostructures: (a) bare surface, (b) phosphoric acid treated sample at 180°C for 20 minutes, (c) after molten KOH dip for 1 minute and (d) after molten KOH dip for 2 minutes.....	123
Figure 5.5	HRXRD Rocking curves of phosphoric acid treated GaN/AlGa _{0.73} N/GaN epilayers: (a) along (002) reflection and (b) along (102) reflection.....	124
Figure 5.6	Schematic of Ga-polar and N-polar (a) GaN film and (b) GaN/AlGa _{0.73} N/GaN heterostructures.....	126
Figure 5.7	Energy band diagram of the pristine AlGa _{0.73} N/AlN/GaN heterostructures.....	127
Figure 5.8	XPS core level spectra of (a) Ga (3d) and (b) Al (2p) of pristine and (c) Ga (3d) and (d) Al (2p) of H ₂ O ₂ treated AlGa _{0.73} N/AlN/GaN HEMT sample.....	129
Figure 5.9	Valence band XPS spectra of (a) pristine and (b) H ₂ O ₂ treated AlGa _{0.73} N/AlN/GaN HEMT sample.....	130
Figure 5.10	Photoluminescence spectroscopy spectra of (a) Pristine and (b) H ₂ O ₂ treated AlGa _{0.73} N/AlN/GaN HEMT sample at room temperature.....	132
Figure 5.11	SPS spectra of (a) pristine and (b) H ₂ O ₂ treated AlGa _{0.73} N/AlN/GaN HEMT sample.....	135
Figure 6.1	(a) The schematic of Al _{0.27} Ga _{0.73} N/GaN HEMT epistack grown on a 200 mm Si (111) substrate. (b) The HRXRD (002) scan of the HEMT stack and (114) RSM data of the layers. (c) The 1.0 μm × 1.0 μm AFM topography of the HEMT stack with an rms roughness of ~0.2 nm, and (d) the schematic of circular gateless HEMT configuration with Ohmic contacts.....	145
Figure 6.2	Fabrication steps of source and drain contacts on Al _{0.27} Ga _{0.73} N/GaN HEMT.....	146
Figure 6.3	Schematic of AlGa _{0.73} N/GaN HEMT epistack grown on sapphire substrate.....	147
Figure 6.4	FESEM image of the fabricated gateless Al _{0.27} Ga _{0.73} N/GaN circular HEMT.....	149
Figure 6.5	Drain current (I _D) as a function of drain source voltage (V _{DS}) of Al _{0.27} Ga _{0.73} N/GaN gateless circular HEMT at room temperature.....	150
Figure 6.6	(a) Drain current (I _D) vs drain source voltage (V _{DS}) as a function of temperature (b) I _{Dsat} vs temperature of Al _{0.27} Ga _{0.73} N/GaN gateless circular HEMT.....	152
Figure 6.7	Transient response of Al _{0.27} Ga _{0.73} N/GaN gateless circular HEMT to UV light at room temperature.....	154

Figure 6.8	Transient response of $\text{Al}_{0.27}\text{Ga}_{0.73}\text{N}/\text{GaN}$ gateless circular HEMT to UV light at (a) $T=150$ K, (b) $T=100$ K...	156
Figure 6.9	Optical Microscopy image of fabricated $\text{Al}_{0.33}\text{Ga}_{0.67}\text{N}/\text{GaN}$ circular HEMT.....	157
Figure 6.10	Optical image of $\text{Al}_{0.33}\text{Ga}_{0.67}\text{N}/\text{GaN}$ circular HEMT for sensing applications.....	157
Figure 6.11	Drain current (I_D) versus drain source voltage (V_{DS}) for $V_{GS}=-8$ V to 0 V of $\text{Al}_{0.33}\text{Ga}_{0.67}\text{N}/\text{GaN}$ circular HEMT.....	158
Figure 6.12	Drain current (I_D) and transconductance (g_m) versus gate source voltage (V_{GS}) of $\text{Al}_{0.33}\text{Ga}_{0.67}\text{N}/\text{GaN}$ circular HEMT	160
Figure 6.13	Forward characteristics (I_G-V_{GS}) of $\text{Al}_{0.33}\text{Ga}_{0.67}\text{N}/\text{GaN}$ circular HEMT at room temperature (linear scale and log scale).....	162
Figure 6.14	Capacitance (C) versus gate source voltage (V_{GS}) of $\text{Al}_{0.33}\text{Ga}_{0.67}\text{N}/\text{GaN}$ circular HEMT.....	164
Figure 6.15	N_{C-V} versus V_{GS} of $\text{Al}_{0.33}\text{Ga}_{0.67}\text{N}/\text{GaN}$ circular HEMT.....	165
Figure 6.16	Transient response of $\text{Al}_{0.33}\text{Ga}_{0.67}\text{N} / \text{GaN}$ circular HEMT to hydrogen gas at room temperature.....	166
Figure 6.17	(a) Schematic of $\text{Al}_{0.33}\text{Ga}_{0.67}\text{N}/\text{GaN}$ circular HEMT hydrogen gas sensor and (b) formation of the dipole interfacial layer.....	167
Figure 6.18	Room temperature transient response of $\text{Al}_{0.33}\text{Ga}_{0.67}\text{N}/\text{GaN}$ circular HEMT to UV light.....	168
Figure 6.19	(a) Schematic of $\text{Al}_{0.33}\text{Ga}_{0.67}\text{N}/\text{GaN}$ circular HEMT UV sensor and (b) carrier transport upon UV illumination...	170

List of Tables

Table 1.1	Gallium nitride material properties and comparison with other semiconducting materials.....	3
Table 1.2	Comparison of properties of substrate materials SiC, sapphire and Si with GaN and AlN.....	4

List of Symbols and Abbreviations

Symbols

S	Source
D	Drain
G	Gate
ω	Omega
φ	Azimuth
χ	Tilt
R_{sh}	Sheet resistance
μ	Mobility
n_s	2DEG sheet carrier concentration
R_H	Hall co-efficient
q	Electronic charge
E_s	Energy of the scattered photon
E_i	Energy of the incident photon
$E_{K.E.}$	Core-shell electron Kinetic energy
E_{Bin}	Core-shell binding energy
ϕ	Work function
$h\nu$	Energy of X-rays
s	Streak spacing
L	Distance between the screen and the sample
a	Intra-row spacing of the atoms
λ	Wavelength
n	Diffraction order
d_{hkl}	Inter-planar distance
Θ	Angle between the incident X-rays and the sample
2Θ	Angle between the incident X-ray beam and the diffracted beam
NH_3	Ammonia
NO_x	Nitrogen oxide
R_{air}	Resistance of air
R_{gas}	Resistance upon exposure to NO_x gas
R_{UV}	Resistance upon exposure to UV light
A_{1g}	Out-of-plane Raman mode
E_{2g}	In-plane Raman mode
σ	Biaxial stress
$\omega - \omega_0$	Frequency difference in the E_2 high peak positions of GaN nanowires and stress free GaN
k_s	Proportionality constant
N_{screw}	Screw dislocations density
N_{edge}	Edge dislocations density
β_{002}	Tilt
β_{102}	Twist
b_{screw}	Length of Burger vector of screw dislocations

b_{edge}	Length of Burger vector of edge dislocations
E_C	Conduction band minimum
E_F	Fermi level
S_V	Surface recombination velocity
D_p	Diffusion co-efficient of the minority carriers
L_p	Diffusion length of the minority carriers
α	Absorption co-efficient
γ	Ratio of PL intensities of H ₂ O ₂ treated sample and as grown sample
k_B	Boltzmann constant
T	Temperature
I_{ph}	Photo generated current
V_{OC}	Open circuit voltage
I_0	Reverse saturation current
A^*	Richardson's constant
ϕ	Surface barrier height
σ_p	Net polarisation charge
d	Thickness of AlGaN layer
ϵ_0	Permittivity of free space
ϵ_{AlGaN}	Permittivity of AlGaN
ΔE_c	Conduction band offset
I_{Dsat}	Saturated drain current
I_D	Drain current
V_{DS}	Drain source voltage
I_0	Photocurrent after illumination is switched off
I_D	Dark current
β	Decay constant
τ	PPC decay time constant
V_{GS}	Gate source voltage
I_{PPC}	Photocurrent
I_{DSS}	Maximum drain current at gate source voltage of 0 V
gm	Transconductance
I_G	Gate current
η	Ideality factor
ϕ_B	Schottky barrier height
A	Area of the device
m^*	Effective mass of charge carriers
h	Planck's constant
$N_{D_{C-V}}$	Doping concentration
w	Depth
C	Capacitance
ϵ_s	Dielectric constant
ΔI	Change in drain current
r_1, r_2	Rate constants

Abbreviations

2D	Two- dimensional
2DEG	Two-dimensional electron gas
AP	Atmospheric pressure
AST	Advanced System Technology
BSFs	Basal-stacking faults
CL	Cathodoluminescence
C-V	Capacitance-Voltage
CVD	Chemical vapor deposition
ESCA	Electron spectroscopy for chemical analysis
FE	Field Emission
FWHM	Full width half maximum
GaCl	Gallium monochloride
GaN	Gallium Nitride
GI	Grazing Incidence
H ₃ PO ₄	Phosphoric acid
HEMTs	High electron mobility transistors
HMDS	Hexamethyldisilazane
HR	High resolution
HVPE	Hydride vapour phase epitaxy
ITO	Indium tin oxide
I-V	Current-Voltage
JCPDS	Joint Committee on Powder Diffraction Standards
KPFM	Kelvin probe force microscopy
LA (M)	longitudinal acoustic mode
LEDs	Light emitting diodes
LP	Low pressure
MBE	Molecular beam epitaxy
MIS	Metal insulator semiconductor
MOCVD	Metal organic chemical vapour deposition
MODFETs	Modulation-doped FET
MoS ₂	Molybdenum disulphide
MOVPE	Metal organic vapour phase epitaxy
NBE	Near band edge
NWs	Nanowires
PA	Plasma assisted
PBN	Pyrolitic boron nitride
PE	Plasma enhanced
PIPS	Precision Ion Polishing System
PL	Photoluminescence
PMGI	Polymethyl glutarimide
PPC	Persistent photoconductivity effect
QCSE	Quantum confined stark effect

RF	Radio Frequency
RHEED	Reflection high energy electron diffraction
SADs	Selected area diffraction patterns
SBH	Surface barrier height
SEM	Scanning electron microscopy
SPS	Surface photovoltage spectroscopy
SPV	Surface photovoltage
TEGFETs	Two-dimensional electron gas field-effect transistors
TEM	Transmission electron microscopy
UV	Ultraviolet
VBM	Valence band maximum
WBDF	Weak- beam dark field
XPS	X-ray photoelectron Spectroscopy
XRD	X-ray diffraction
2D	Two- dimensional
2DEG	Two-dimensional electron gas
C-V	Capacitance-Voltage
CVD	Chemical vapour deposition
FE	Field Emission
GaCl	Gallium monochloride
GaN	Gallium Nitride
HEMTs	High electron mobility transistors
HVPE	Hydride vapour phase epitaxy
MBE	Molecular beam epitaxy
MOCVD	Metal organic chemical vapour deposition
MODFETs	Modulation-doped FET
MOVPE	Metal organic vapour phase epitaxy
NWs	Nanowires
QCSE	Quantum confined stark effect
SEM	Scanning electron microscopy
TEGFETs	Two-dimensional electron gas field-effect transistors